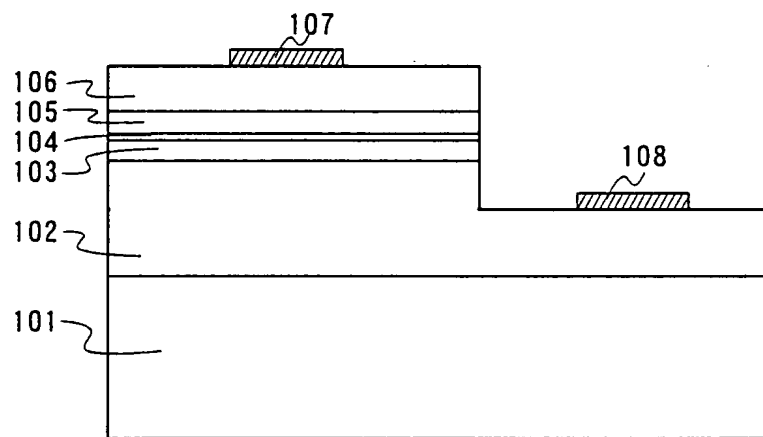


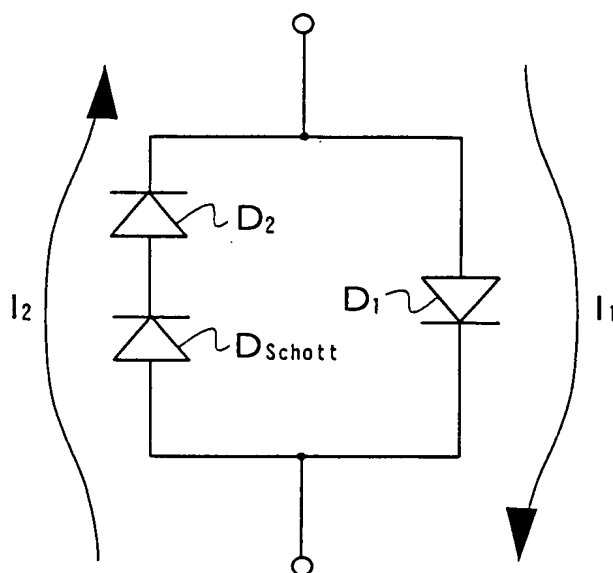
FIG. 1



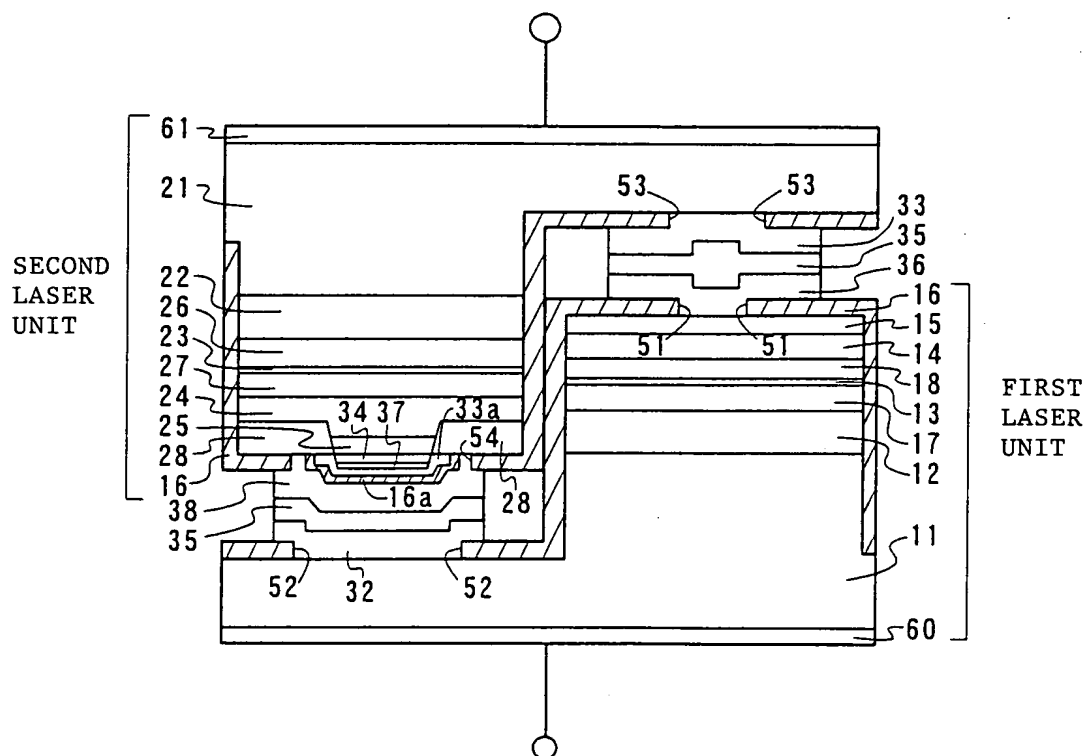
09516731.0301.00

A detailed cross-sectional view of a laser device assembly. The assembly is housed within a rectangular frame (11, 60). On the left, a vertical component (21) is shown with internal layers (22, 23, 24, 25). A horizontal component (16) is positioned below it. The central part of the assembly features a complex structure with multiple layers and components, including a central block (51) and surrounding layers (52, 53, 54). On the right, a vertical component (31) is shown with internal layers (32, 33, 34, 35). The entire assembly is labeled "FIRST LASER UNIT" on the right side. Electrical connections are shown at the top and bottom of the assembly.

SECRET



SECRET



This cross-sectional view shows a trench structure within a substrate. The substrate is labeled 16. A central layer, labeled 25, is positioned within the trench. The side walls of the trench are labeled 71 and 72. The bottom of the trench is labeled 73. A layer, labeled 34, is located between the side walls 71 and 72. A layer, labeled 37, is located between the side walls 72 and 73. A layer, labeled 33a, is located between the side walls 73 and 71. A layer, labeled 16a, is located between the side walls 71 and 72. A layer, labeled 38, is located between the side walls 72 and 73. A layer, labeled 35, is located between the side walls 73 and 71. A layer, labeled 54, is located between the side walls 71 and 72. A layer, labeled 28, is located between the side walls 72 and 73. A layer, labeled 24, is located between the side walls 73 and 71. Two upward arrows are shown above the trench structure.

Figure 1 is a schematic diagram of a multi-layered structure 10. The structure is composed of several horizontal layers. At the top is layer 11. Below it is a section 12, which contains three distinct horizontal layers labeled 13, 14, and 15 from top to bottom. The entire assembly is labeled 10 at the bottom right. A wavy arrow labeled 1 points to the left side of the structure.

FIG. 8

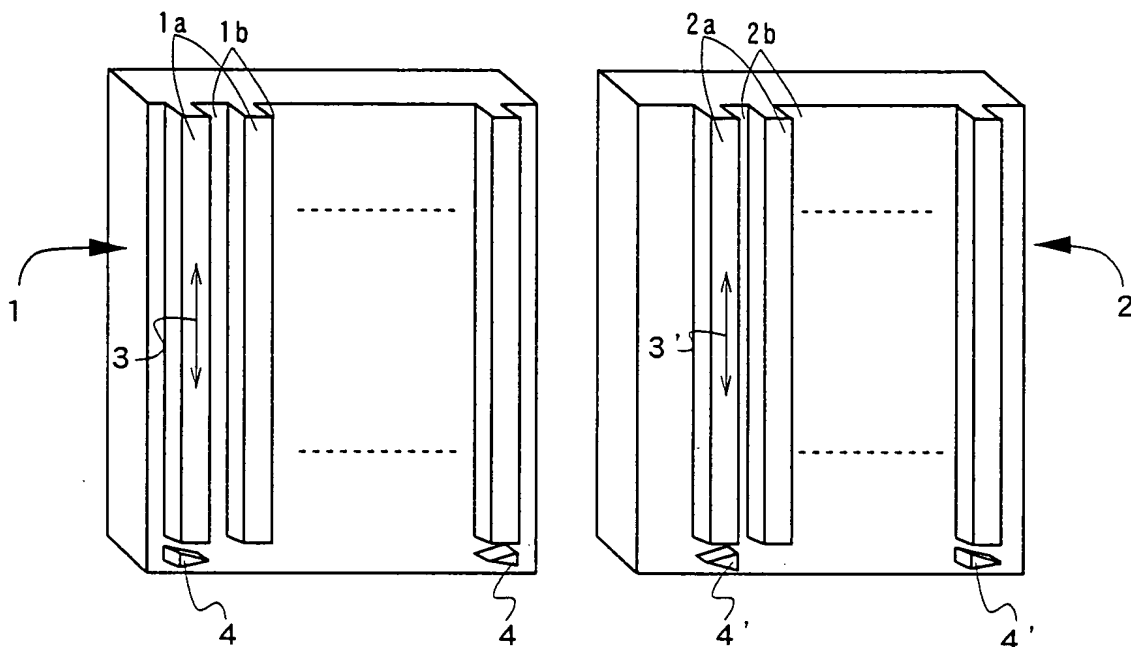
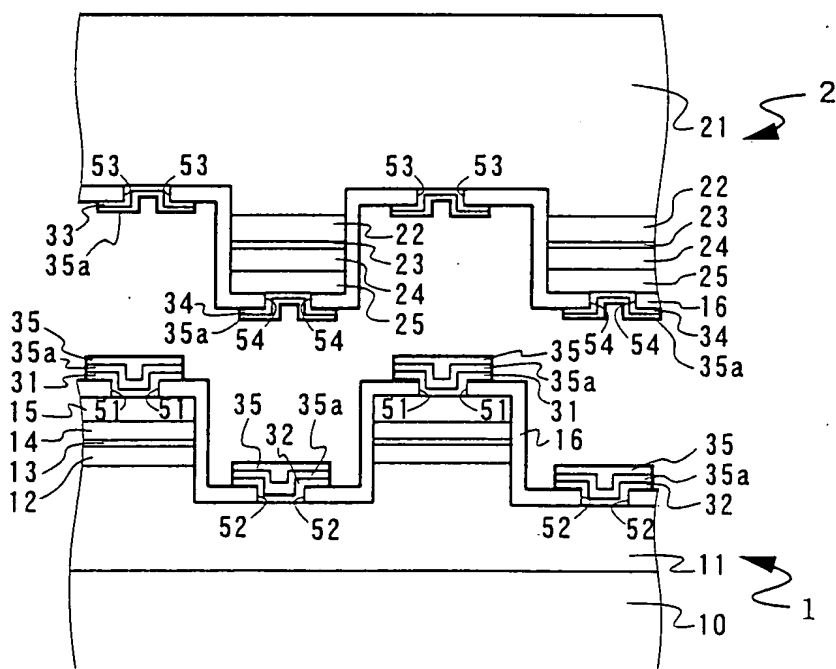


FIG. 9



09546734.030400

This cross-sectional view shows a semiconductor device with a central raised portion. The device is bounded by a top layer 61 and a bottom layer 60. The central portion is raised above the surrounding surface. On the left and right sides of this central portion, there are structures labeled 15, 14, 13, and 12. The central portion itself has a top surface 31 and is surrounded by a layer 16. Below the central portion, there are layers 32, 35, and 34. On the right side, there are additional layers 22, 23, 24, and 25. The entire device is shown within a frame 1.